MMBD352LT1G, MMBD353LT1G, NSVMMBD353LT1G, MMBD354LT1G, NSVMMBD354LT1G, MMBD355LT1G

Dual Hot Carrier Mixer Diodes

These devices are designed primarily for UHF mixer applications but are suitable also for use in detector and ultra-fast switching circuits.

Features

- Very Low Capacitance Less Than 1.0 pF @ Zero V
- Low Forward Voltage 0.5 V (Typ) @ $I_F = 10 \text{ mA}$
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_{R}	7.0	V_{CC}

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,	P_{D}		
(Note 1) T _A = 25°C Derate above 25°C		225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{0JA}	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

- 1. FR-5 = 1.0 x 0.75 x 0.062 in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

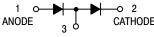


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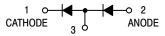


SOT-23 (TO-236) CASE 318



CATHODE/ANODE

MMBD352LT1G STYLE 11

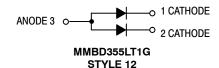


CATHODE/ANODE

MMBD353LT1G NSVMMBD353LT1G STYLE 19



MMBD354LT1G NSVMMBD354LT1G STYLE 9



MARKING DIAGRAM



Mxx = Device Code M = Date Code*

■ = Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

$\begin{array}{c} \textbf{MMBD352LT1G, MMBD353LT1G, NSVMMBD353LT1G, MMBD354LT1G, NSVMMBD354LT1G, MMBD355LT1G} \end{array}$

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted) (EACH DIODE)

Rating	Symbol	Min	Max	Unit
Forward Voltage (I _F = 10 mAdc)	V _F	-	0.60	V
Reverse Leakage Current (Note 3) (V _R = 3.0 V) (V _R = 7.0 V)	I _R	- -	0.25 10	μΑ
Capacitance (V _R = 0 V, f = 1.0 MHz)	С	-	1.0	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. For each individual diode while the second diode is unbiased.

ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
MMBD352LT1G	M5G	SOT-23 (Pb-Free)	3,000 Units / Tape & Reel
MMBD352LT3G	M5G	SOT-23 (Pb-Free)	10,000 Units / Tape & Reel
MMBD353LT1G	M4F	SOT-23 (Pb-Free)	3,000 Units / Tape & Reel
NSVMMBD353LT1G	M4F	SOT-23 (Pb-Free)	3,000 Units / Tape & Reel
MMBD353LT3G	M4F	SOT-23 (Pb-Free)	10,000 Units / Tape & Reel
MMBD354LT1G	М6Н	SOT-23 (Pb-Free)	3,000 Units / Tape & Reel
NSVMMBD354LT1G	М6Н	SOT-23 (Pb-Free)	3,000 Units / Tape & Reel
MMBD355LT1G	MJ1	SOT-23 (Pb-Free)	3,000 Units / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

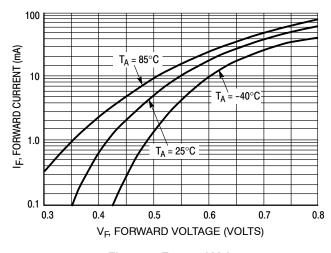


Figure 1. Forward Voltage

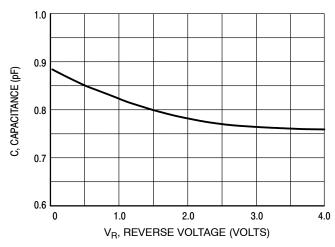


Figure 2. Capacitance



SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

DATE 30 JAN 2018

SCALE 4:1 D - 3X b

TOP VIEW







RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,

	PROT	RUSIONS, OR GATE BURRS.	
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	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE
OT (1 F O			

SOT-23 (TO-236)

STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
ANODE	SOURCE	CATHODE	CATHODE	2. DRAIN	2. GATE
CATHODE	3. GATE	CATHODE-ANODE	ANODE	3. GATE	ANODE

STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
CATHODE	CATHODE	2. ANODE	CATHODE	2. ANODE	ANODE
ANODE	CATHODE	CATHODE	ANODE	CATHODE-ANOD	E 3. GATE

STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
SOURCE	OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3 DRAIN	3 INPLIT	3 CATHODE	3. SOURCE	3. GATE	NO CONNECTION

STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE	
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PAGE 1 OF 1

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